



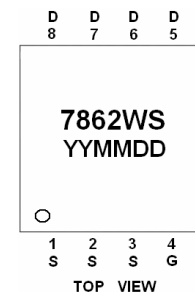
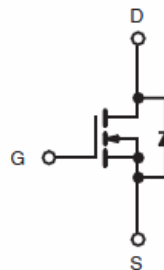
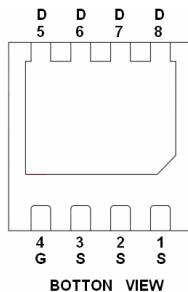
General Description

AFN7862WS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 60V/ 8.7A, $R_{DS(ON)}=15m\Omega@V_{GS}=10V$
- 60V/ 7.3A, $R_{DS(ON)}=17m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3X3-8L package design

Pin Description (DFN3X3-8L)



Application

- Primary Side Switch
- Synchronous Rectification
- DC/DC Converters & DC/AC Inverters
- Boost Converters

Pin Define

Pin	Symbol	Description
1~3	S	Source
4	G	Gate
5~8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN7862WSFN338RG	7862WS	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code

※ MM month code

※ DD date code

※ AFN7862WSFN338RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	11	A
		8	
Pulsed Drain Current	I _{DM}	90	A
Continuous Source Current(Diode Conduction)	I _S	3.2	A
Power Dissipation	P _D	3.8	W
		2	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	t ≤ 10 s	26	°C/W
Thermal Resistance-Junction to Case	Steady-State	1.9	

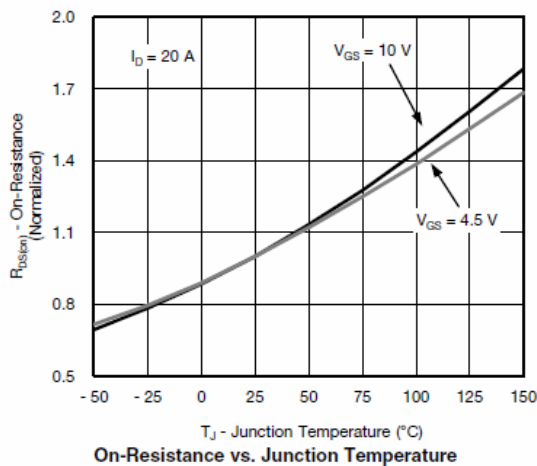
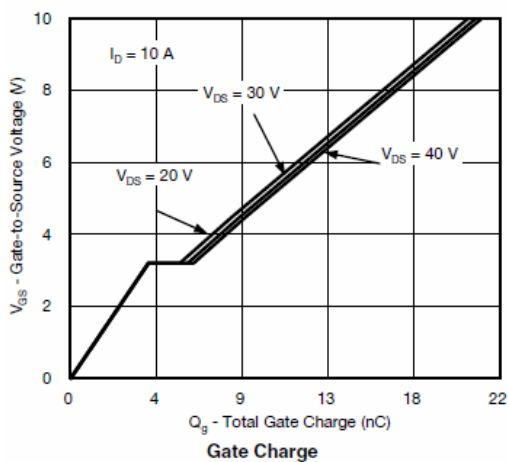
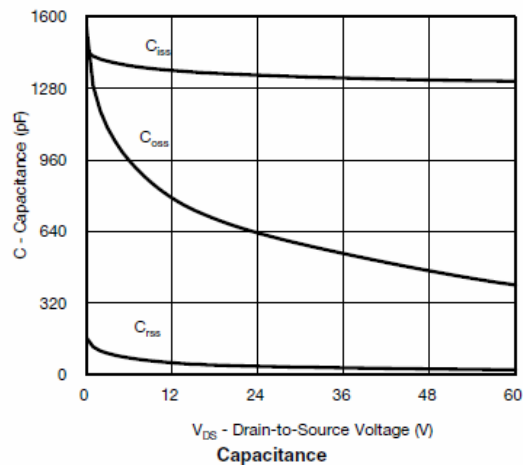
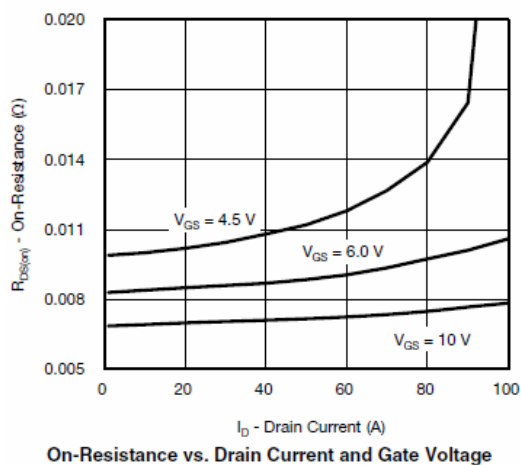
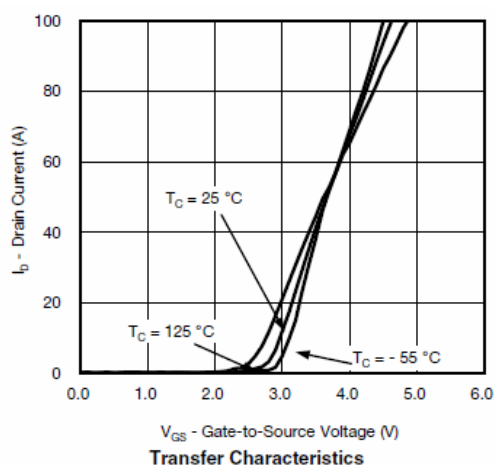
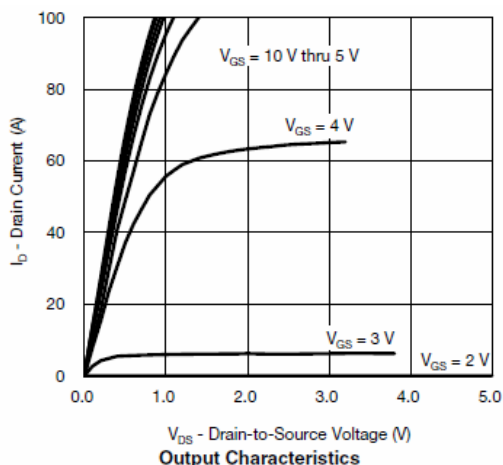
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0		2.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	uA
		V _{DS} =48V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =10V	20			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8.7A		12	15	mΩ
		V _{GS} =4.5V, I _D =7.3A		14	17	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10A		24		S
Diode Forward Voltage	V _{SD}	I _S =2.0A, V _{GS} =0V		0.85	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =4.5V I _D ≡10A		10	20	nC
Gate-Source Charge	Q _{gs}			5		
Gate-Drain Charge	Q _{gd}			4		
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V f=1MHz		1350		pF
Output Capacitance	C _{oss}			450		
Reverse Transfer Capacitance	C _{rss}			40		
Turn-On Time	t _{d(on)}	V _{DD} =30V, R _L =3Ω I _D ≡10A, V _{GEN} =10V R _G =1Ω		25	50	ns
	t _r			100	200	
Turn-Off Time	t _{d(off)}			25	50	
	t _f			10	20	

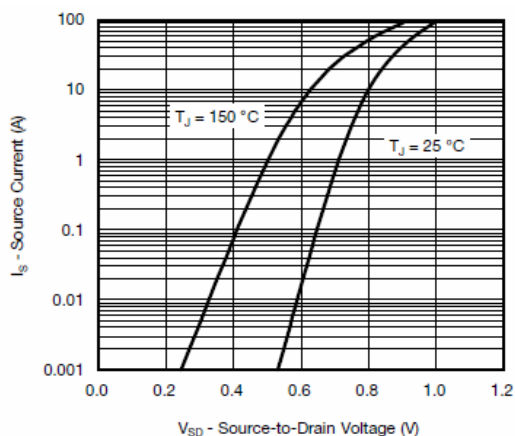


Typical Characteristics

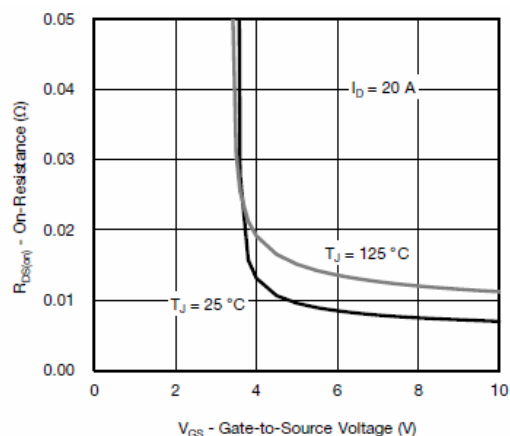




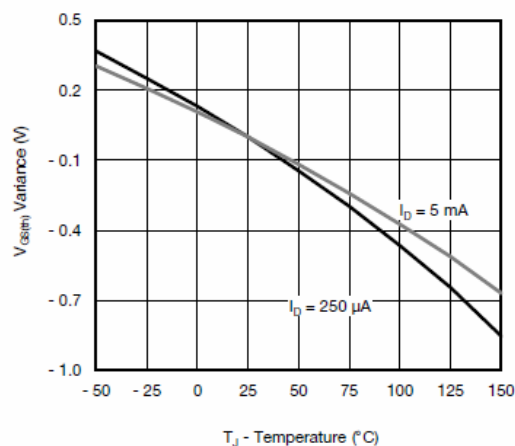
Typical Characteristics



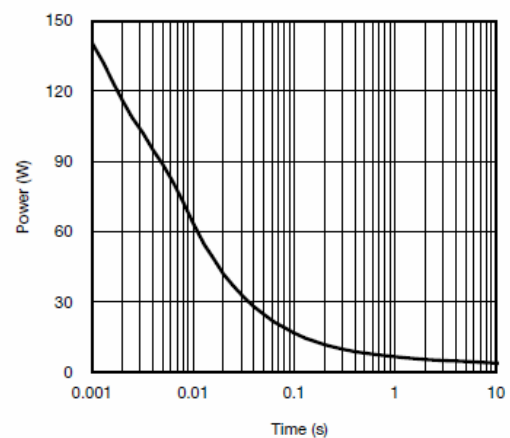
Source-Drain Diode Forward Voltage



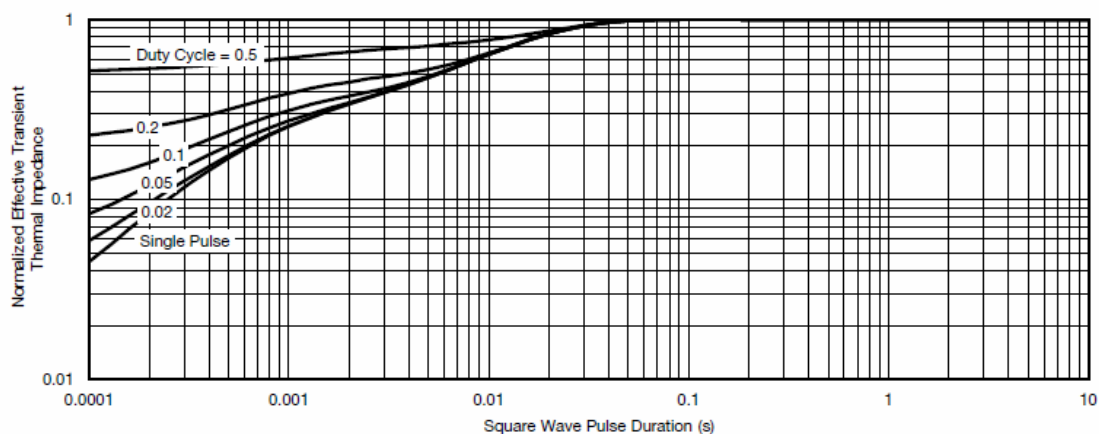
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

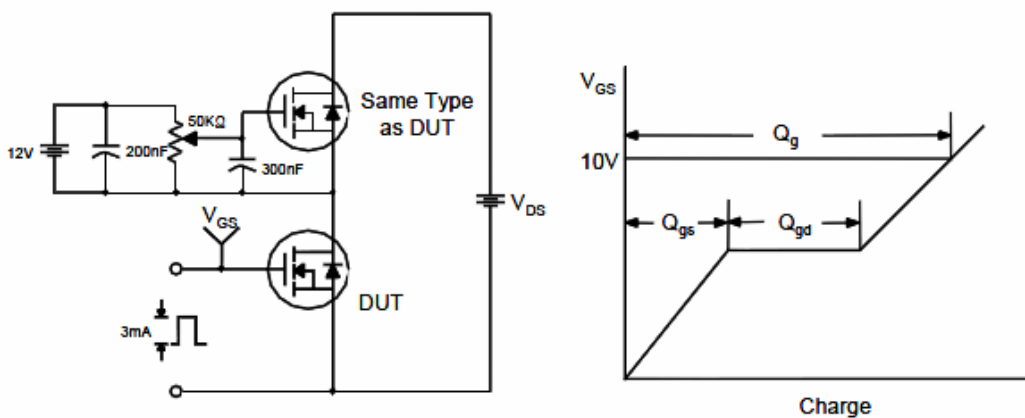


Normalized Thermal Transient Impedance, Junction-to-Case

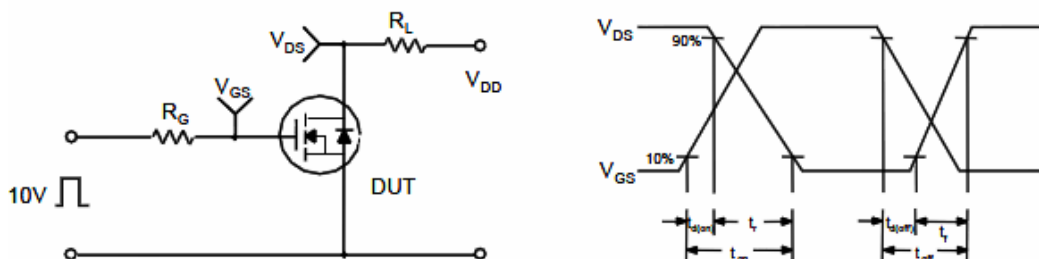


Typical Characteristics

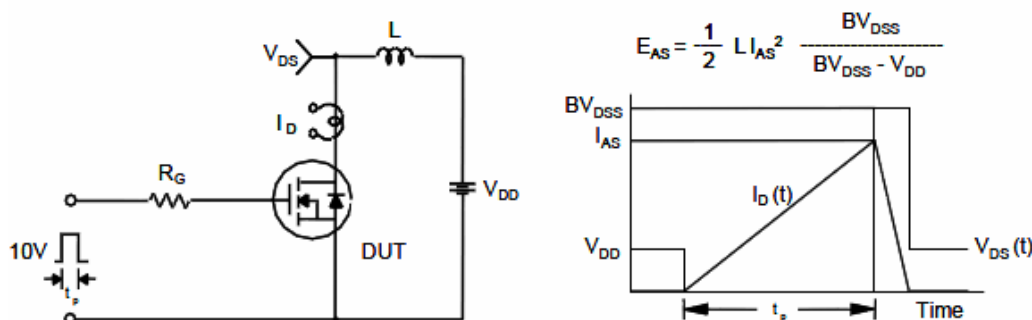
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

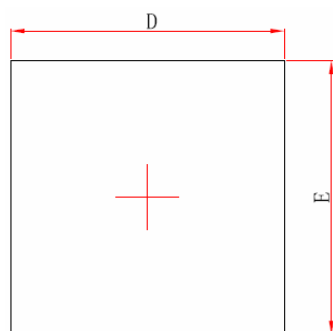


Unclamped Inductive Switching Test Circuit & Waveforms

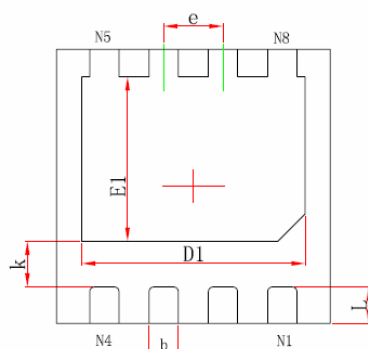




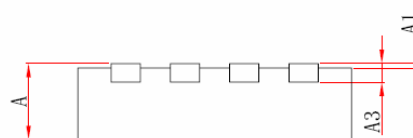
Package Information (DFN3X3-8L)



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.800	0.900	0.031	0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.350	2.550	0.093	0.100
E1	1.700	1.900	0.067	0.075
k	0.450	0.550	0.018	0.022
b	0.270	0.370	0.011	0.015
e	0.650TYP.		0.026TYP.	
L	0.324	0.476	0.013	0.019

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